

Automotive N-Channel 55 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	55
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.006
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.010
I_D (A)	110
Configuration	Single

FEATURES

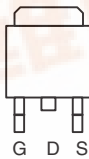
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified^c

AUTOMOTIVE
GRADE

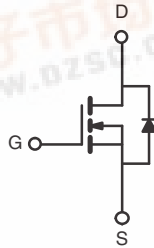


RoHS
COMPLIANT
HALOGEN
FREE

TO-263



Top View



N-Channel MOSFET

ORDERING INFORMATION

Package	TO-263
Lead (Pb)-free and Halogen-free	SQM110N05-06L-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	55	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25$ °C	110
		$T_C = 125$ °C	64
Continuous Source Current (Diode Conduction)	I_S	120	A
Pulsed Drain Current ^a	I_{DM}	443	
Single Pulse Avalanche Energy	I_{AS}	61	
Single Pulse Avalanche Current	E_{AS}	186	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	157
		$T_C = 125$ °C	52
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.95	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



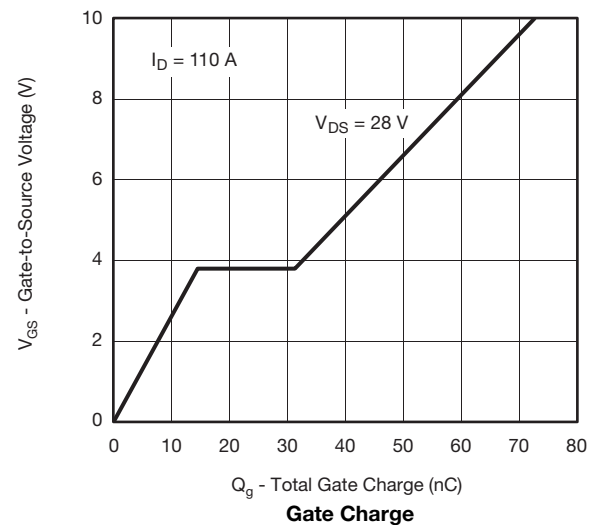
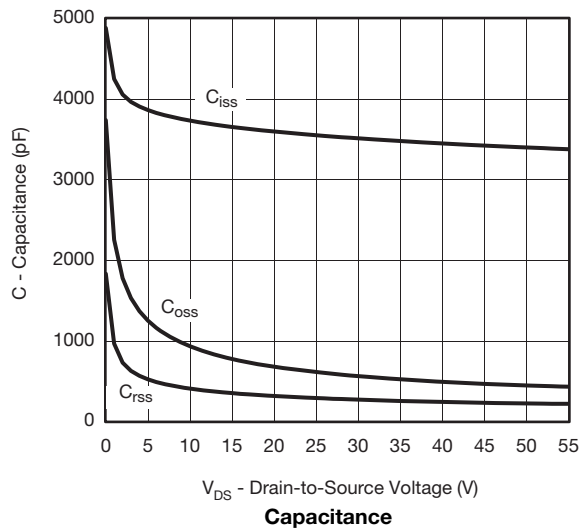
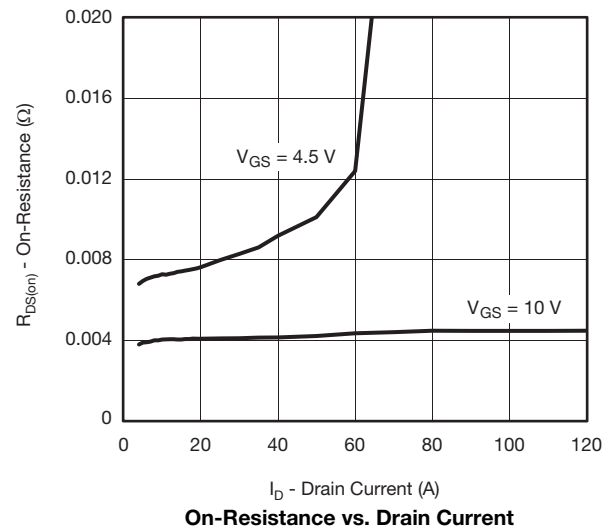
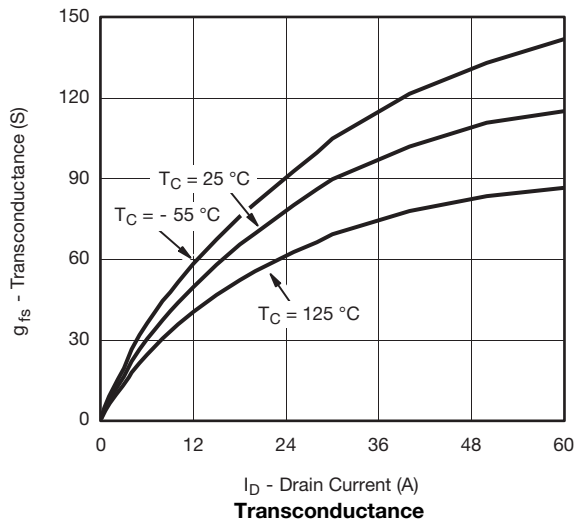
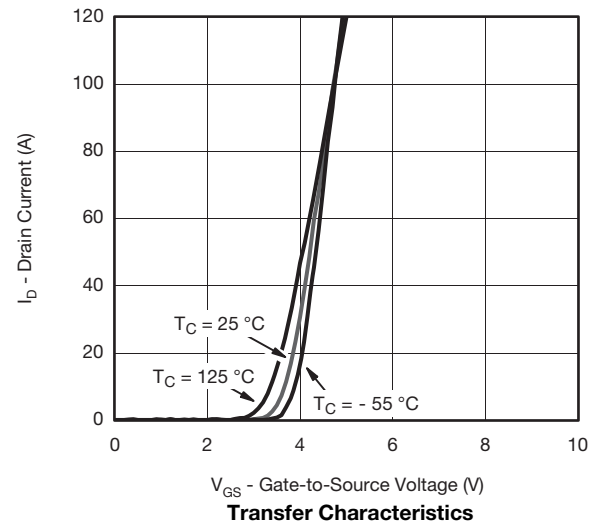
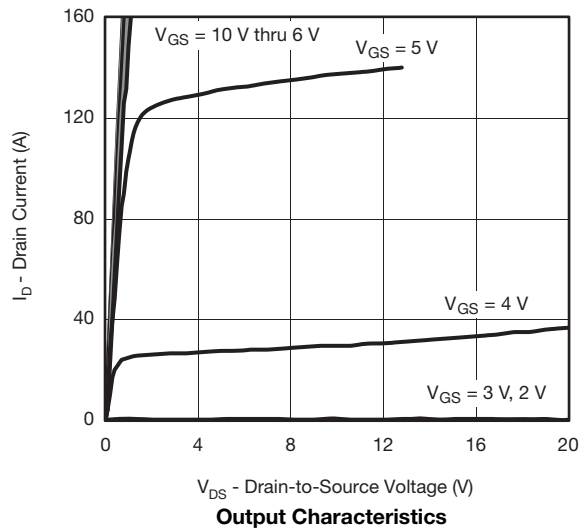
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		55	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 55 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 55 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 55 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.0047	0.006	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0105	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0132	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.008	0.010	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	90	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	3550	4440	pF
Output Capacitance	C _{oss}			-	610	765	
Reverse Transfer Capacitance	C _{rss}			-	288	360	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 28 V, I _D = 110 A	-	73	110	nC
Gate-Source Charge ^c	Q _{gs}			-	14.5	-	
Gate-Drain Charge ^c	Q _{gd}			-	16.8	-	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 28 V, R _L = 0.25 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _g = 2.5 Ω		-	12	18	ns
Rise Time ^c	t _r			-	13	20	
Turn-Off Delay Time ^c	t _{d(off)}			-	37	56	
Fall Time ^c	t _f			-	13	20	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	443	A
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0 V		-	0.9	1.5	V

Notes

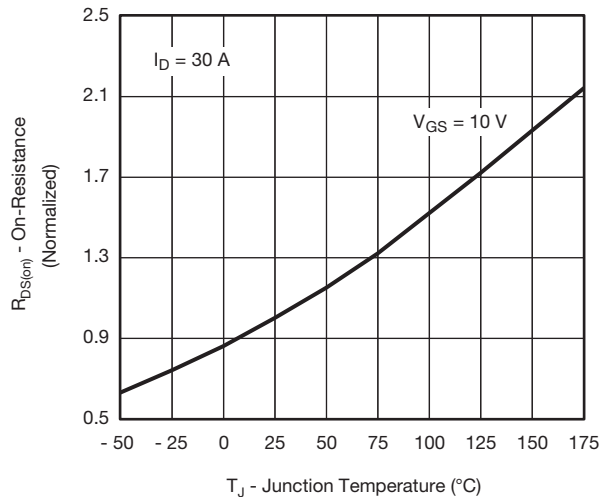
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

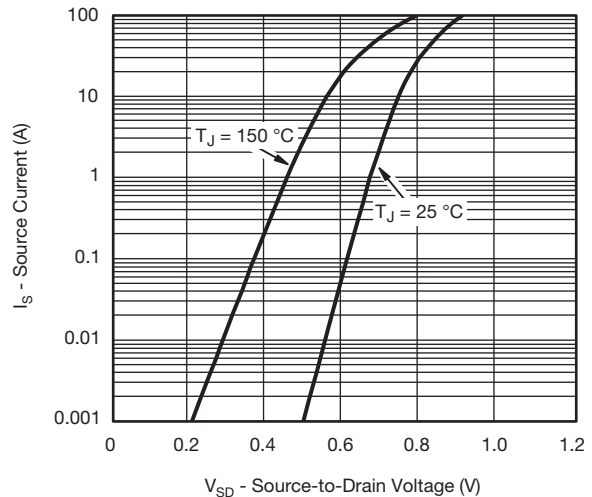
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



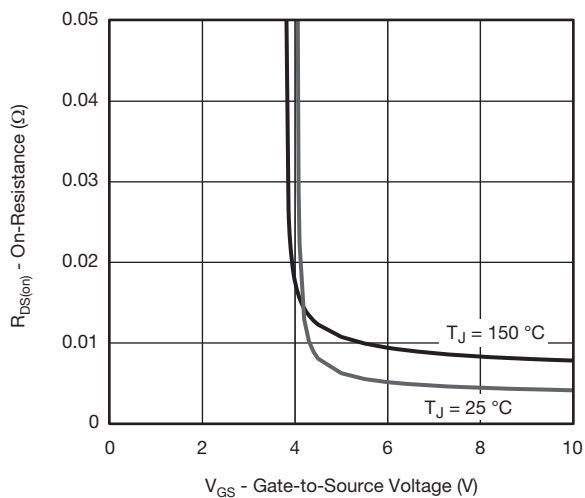
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



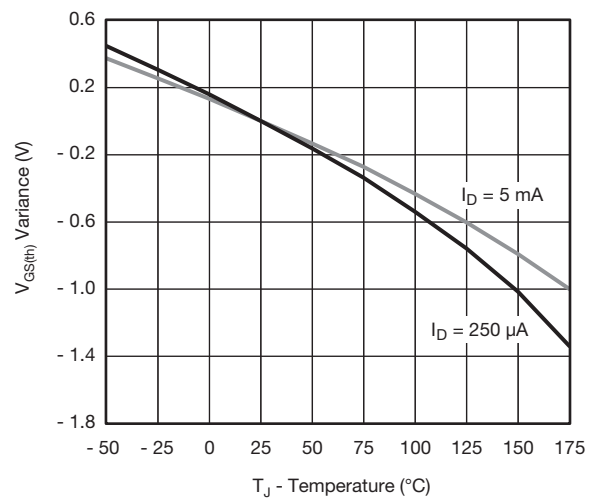
On-Resistance vs. Junction Temperature



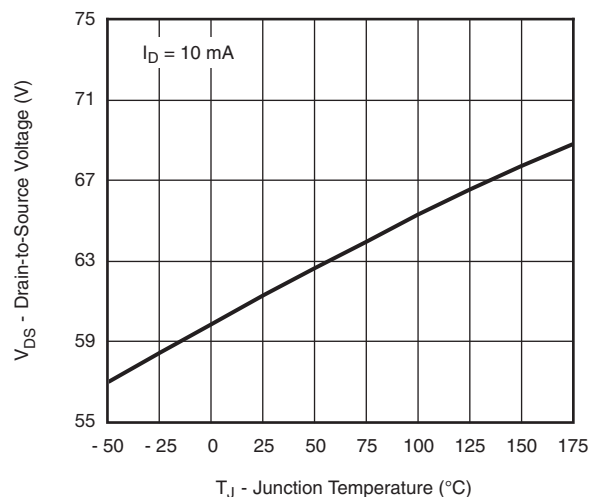
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

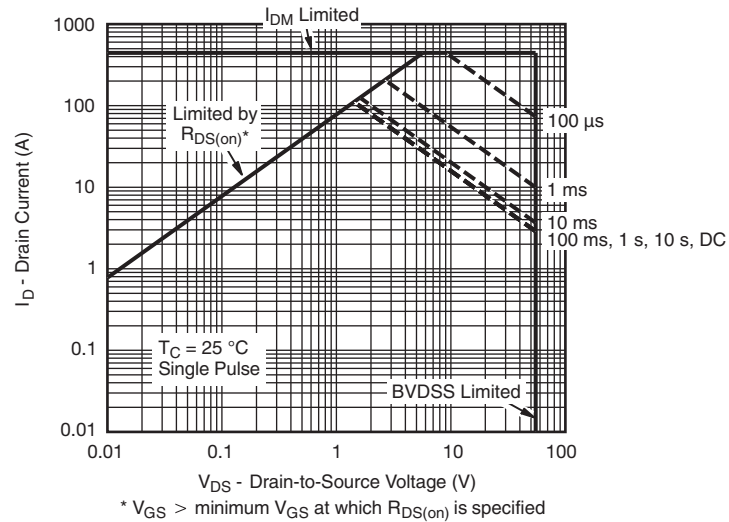


Threshold Voltage

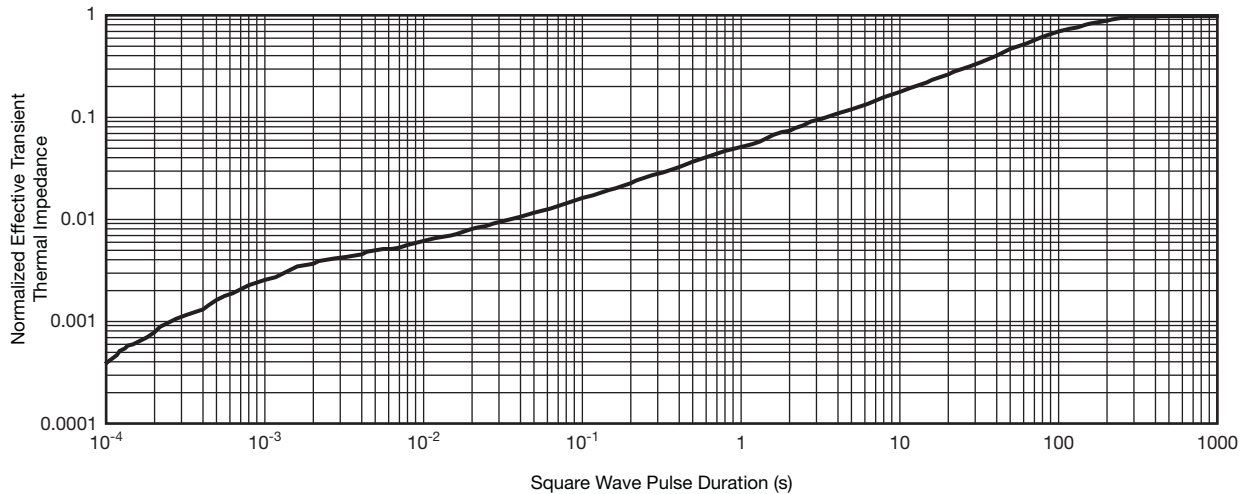


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

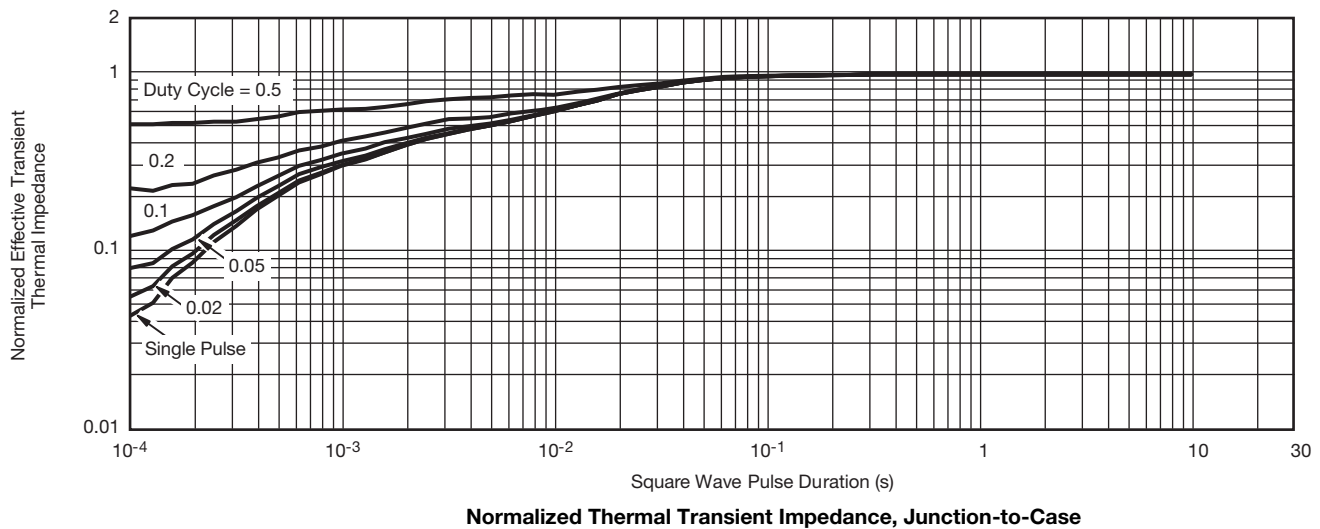


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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